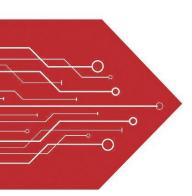
# MSKSEMI















**ESD** 

**TVS** 

**TSS** 

MOV

**GDT** 

**PLED** 

Broduct data speet



## **FEATURES**

- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement



## **PINNING**

MARK:T3

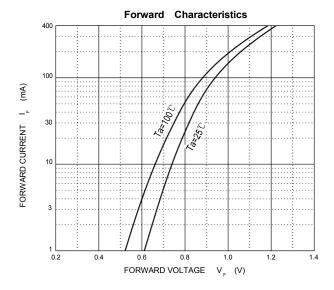
PIN	DESCRIPTION	
1	Cathode	
2	Anode	

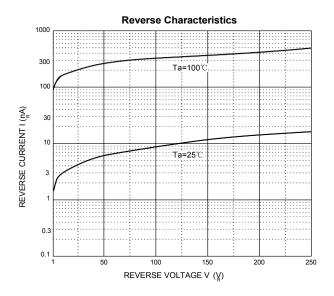
## Absolute Maximum Ratings at 25 °C

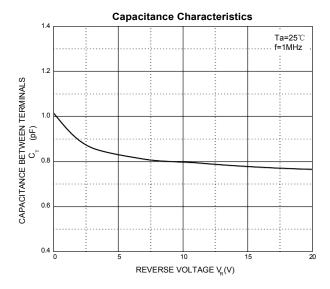
Parameter	Symbols	BAV21W	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	250	V
Maximum RMS voltage	V <sub>RMS</sub>	200	V
Continuous Forward Current	I <sub>F</sub>	250	mA
Repetitive Peak Forward Current	I <sub>FRM</sub>	625	mA
Non-reptitive Peak Forward Surge Current at 1ms at 1 us	I <sub>FSM</sub>	1 3 9	А
Total Power Dissipation	P <sub>tot</sub>	500	mW
Operating and Storage Temperature Range	$T_j$ , $T_{stg}$	-55 ~ +150	°C

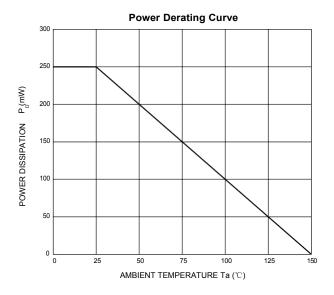
## Characteristics at T<sub>a</sub> = 25 °C

Parameter	Symbols	BAV21W	Units
Reverse BreakdownVoltage at I <sub>R</sub> =100µA	$V_{(BR)R}$	250	V
Maximum Forward Voltage at 100 mA at 200 mA	V <sub>F</sub>	1.00 1.25	V
Maximum DC Reverse Current T <sub>a</sub> = 25 °C at Rated DC Blocking Voltage T <sub>a</sub> =150 °C	I <sub>R</sub>	0.1 100	μΑ
Typical Junction Capacitance at V <sub>R</sub> =4V, f=1MHz	Cj	5	pF
Maximum Reverse Recovery Time	t <sub>rr</sub>	50	ns



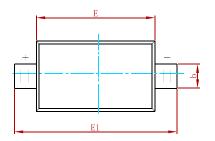


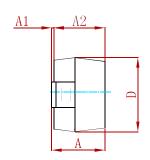


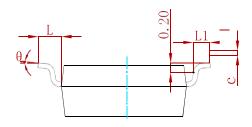




## PACKAGE MECHANICAL DATA

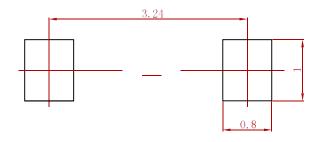






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
С	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

## **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
BAV21W-MS	SOD-123	3000



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